

This listing of claims will replace all prior versions of claims in the application.

Claims 1-44. (cancelled)

Claim 45. (currently amended) A chemically-amplified positive-acting photoresist composition comprising:

a) a resin that comprises photoacid-labile groups; and
b) one or more photoacid generator compounds other than a N-oxyimidosulfonate that upon exposure to activating radiation generate an acid of the formula $R(CR^1R^2)CF_2SO_3H$ where R is optionally substituted alkyl having 4 to about 20 carbon atoms, optionally substituted alicyclic group, optionally substituted carbocyclic aryl group, optionally substituted heteroalicyclic group, or optionally substituted heteroaromatic group, and R is not perhaloalkyl; and

R^1 and R^2 are each independently hydrogen or non-hydrogen substituent,

Claim 46. (previously presented) The photoresist composition of claim 45 wherein R is optionally substituted alkyl.

Claim 47. (previously presented) The photoresist composition of claim 45 wherein R is an optionally substituted alicyclic group.

Claim 48. (previously presented) The photoresist composition of claim 45 wherein R is an optionally substituted carbocyclic aryl group.

Claim 49. (previously presented) The photoresist composition of claim 45 wherein R is an optionally substituted heteroalicyclic group, or optionally substituted heteroaromatic group.

Claim 50. (previously presented) The photoresist composition of claim 45 wherein the one or more photoacid generator compounds are iodonium compounds.

Claim 51. (previously presented) The photoresist composition of claim 45 wherein the one or more photoacid generator compounds are sulfonium compounds.

Claim 52. (previously presented) The photoresist of claim 45 wherein the one or more photoacid generators are non-ionic compounds.

Claim 53. (currently amended) The photoresist composition of claim 45 52 wherein the one or more photoacid generator compounds are sulfonate compounds.

Claim 54. (cancelled)

Claim 55. (currently amended) The photoresist composition of claim 45 wherein the one or more photoacid generator compounds are diazosulfone compounds.

Claim 56. (previously presented) The photoresist composition of claim 45 wherein the resin comprises phenolic groups.

Claim 57. (previously presented) The photoresist composition of claim 45 wherein the resin is at least substantially free of aromatic groups.

Claim 58. (previously presented) The photoresist of claim 45 wherein the resin is completely free of aromatic groups.

Claim 59. (previously presented) An article of manufacture comprising a coating layer of a photoresist composition of claim 45.

Claim 60. (previously presented) The article of manufacture of claim 59
wherein the article is a microelectronic wafer substrate.